1SS181

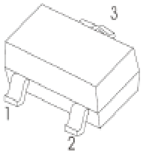
SWITCHING DIODES

康 比 電 子
HORNBY ELECTRONIC

FEATURES

- **Low forward: VF(3)=0.92V(typ)**
- **Fast reverse recovery time: trr=1.6ns(typ)**
- **Marking: A3**

SOT-23



1. BASE
2. EMITTER
3. COLLECTO

Maximum Ratings @T_A=25℃

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	VRM	85	V
DC Blocking Voltage	VR	80	V
Forward Continuous Current	IFM	300	mA
Average Rectified Output Current	IO	100	mA
Power Dissipation	PD	150	mW
Junction temperature	TJ	125	℃
Storage temperature range	TSTG	-55-125	℃

Electrical Characteristics @T_A=25℃

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V (BR)R	80			V	IR=100μA
Forward voltage	VF1		0.61		V	IF=1mA
	VF2		0.74		V	IF=10mA
	VF3		0.92	1.2	V	IF=100mA
Reverse current	IR1			0.1	uA	VR=30V
	IR2			1.0	uA	VR=80V
Capacitance between terminals	CT		2.2	4.0	pF	VR=0,f=1MHz
Reverse recovery time	trr		1.6	4.0	ns	IF=IR=10mA,Irr=0.1×IR

Typical Characteristics